

N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.008 at $V_{GS} = 10$ V	18
	0.011 at $V_{GS} = 4.5$ V	15

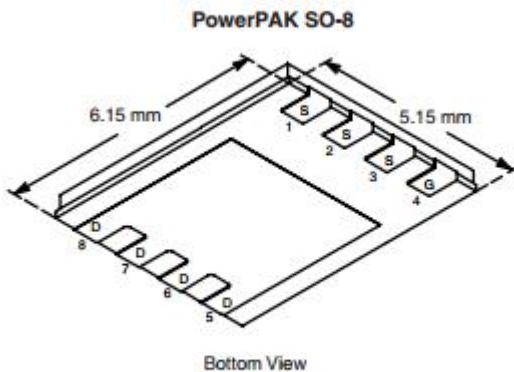
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- PWM Optimized for High Efficiency
- New Low Thermal Resistance
- PowerPAK[®] Package with Low 1.07 mm Profile
- 100 % R_g Tested

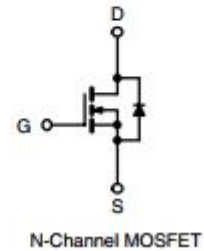


APPLICATIONS

- Buck Converter
 - High Side or Low Side
- Synchronous Rectifier
 - Secondary Rectifier



Ordering Information: Si7860DP-T1
Si7860DP-T1-E3 (Lead (Pb)-free)
Si7860DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	18	11
		$T_A = 70$ °C	15	8
Pulsed Drain Current	I_{DM}	± 50		A
Continuous Source Current (Diode Continuous) ^a	I_S	4.1	1.5	
Avalanche Current	I_{AS}	30		
Single Pulse Avalanche Energy	E_{AS}	45		mJ
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	5	1.8
		$T_A = 70$ °C	3.2	1.1
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}		260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^a	$t \leq 10$ s	R_{thJA}	20	25	°C/W
	Steady State		56	70	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.8	2.3	

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

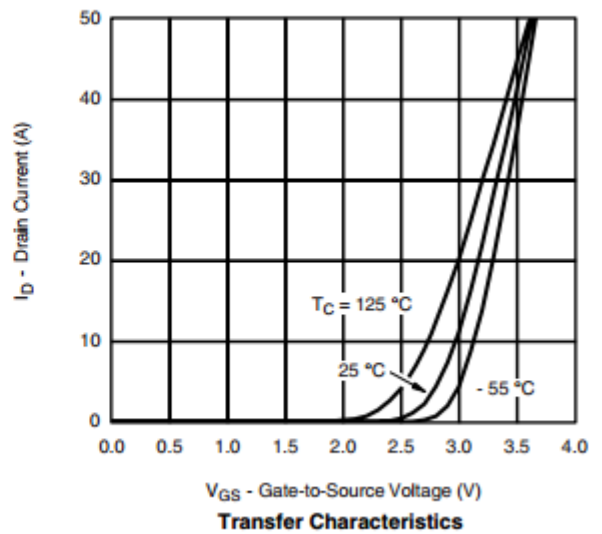
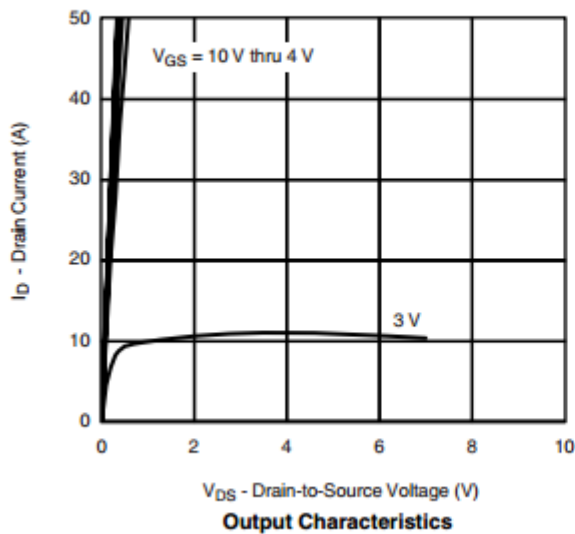
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 18\text{ A}$		0.0066	0.008	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0090	0.011	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 18\text{ A}$		60		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 3\text{ A}, V_{GS} = 0\text{ V}$		0.70	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 18\text{ A}$		13	18	nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			4.0		
Gate Resistance	R_g		0.5	1.7	3.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D = 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		18	27	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			46	70	
Fall Time	t_f			19	30	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		40	70	

Notes:

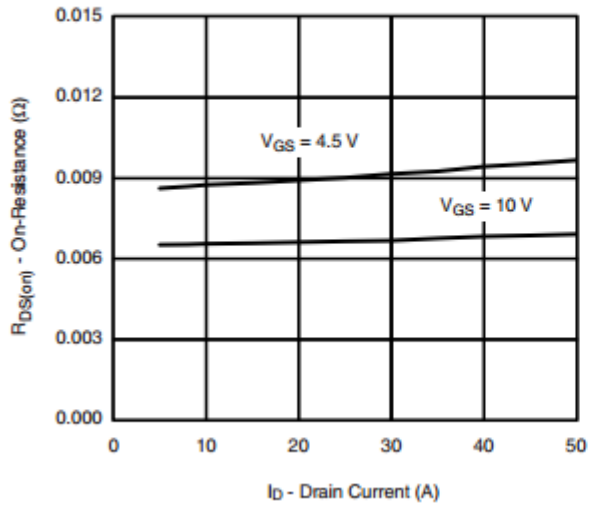
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

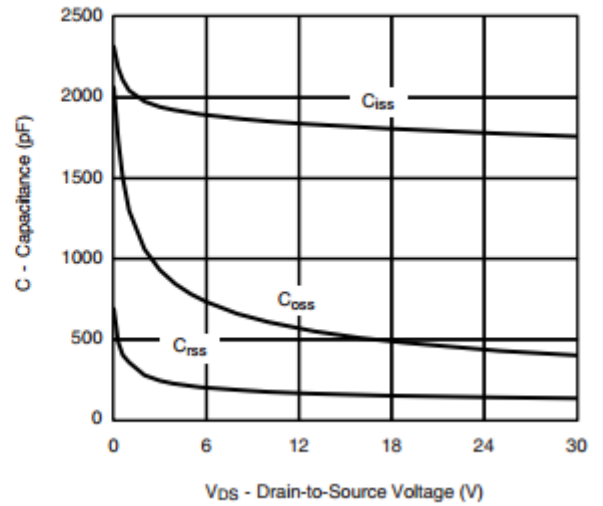
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



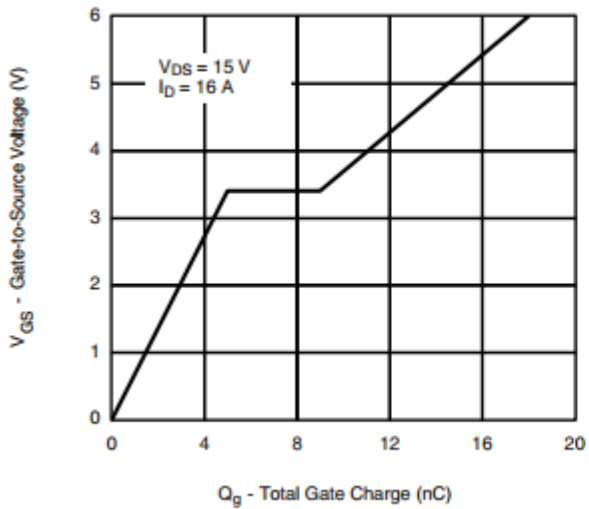
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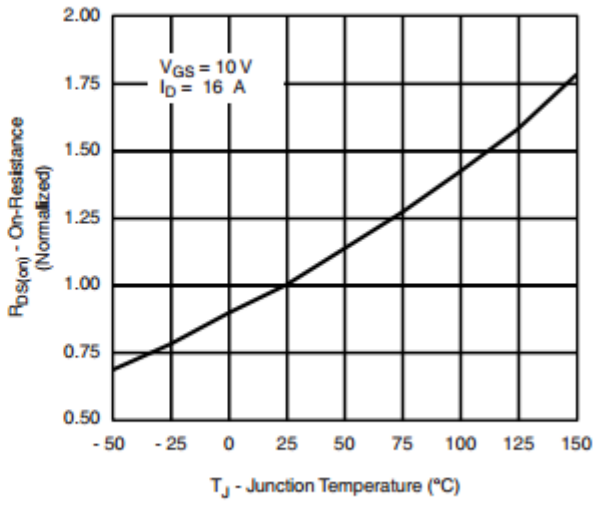
On-Resistance vs. Drain Current



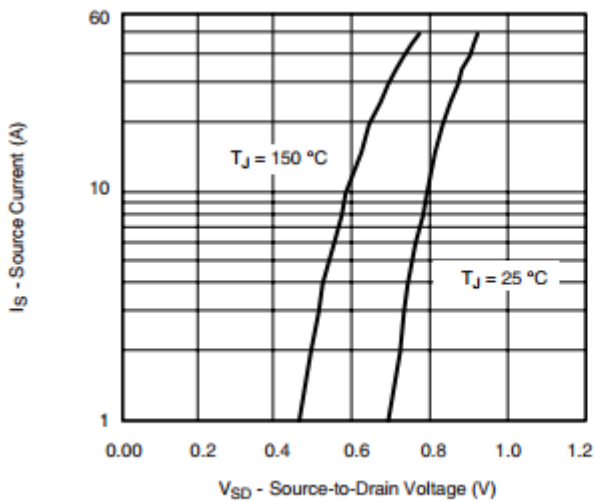
Capacitance



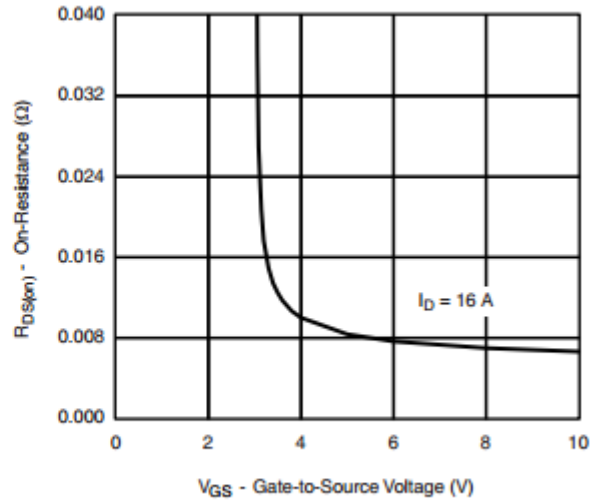
Gate Charge



On-Resistance vs. Junction Temperature

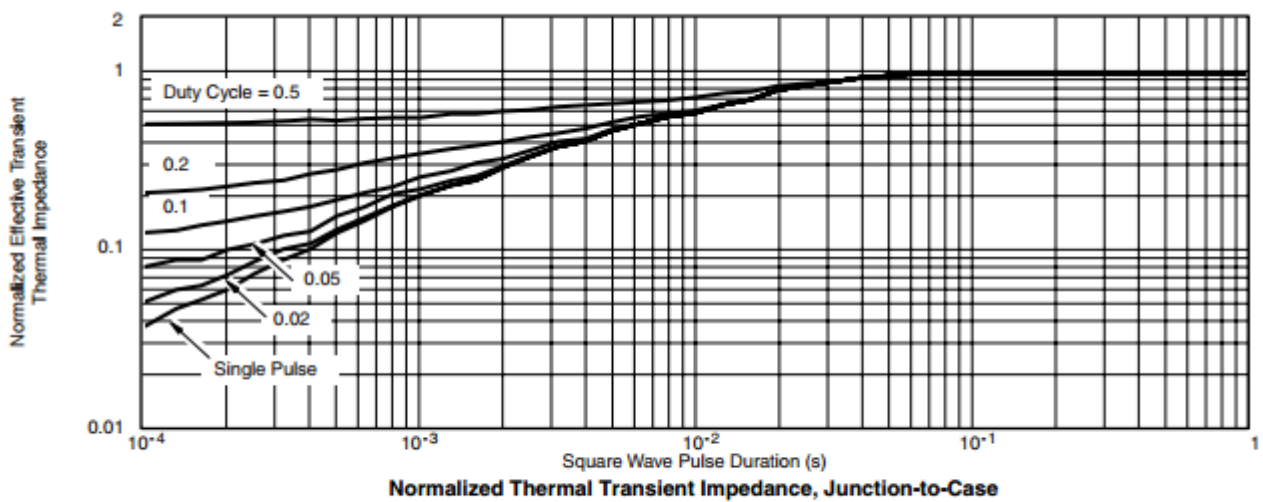
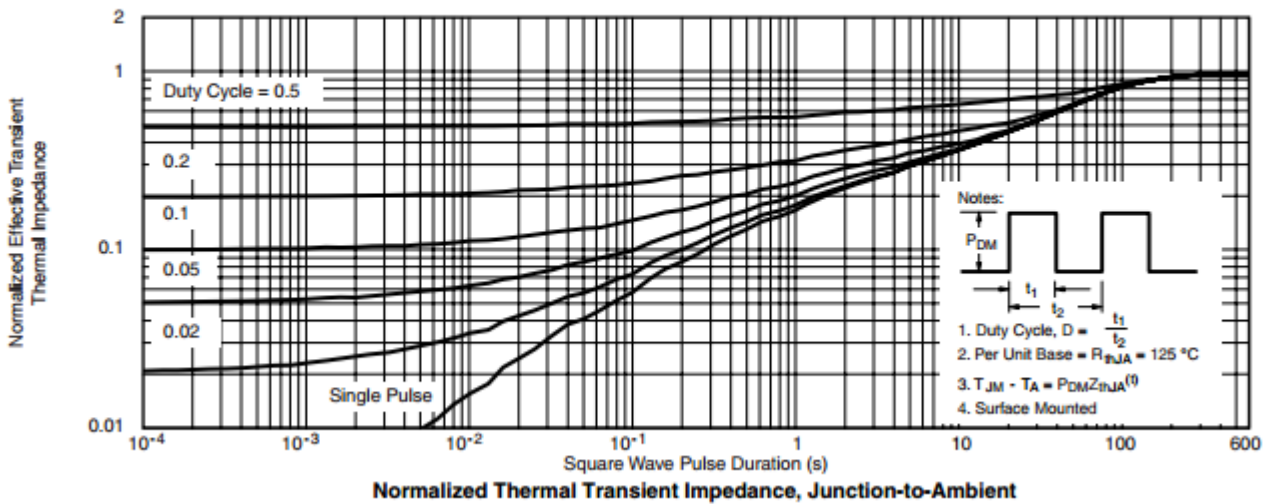
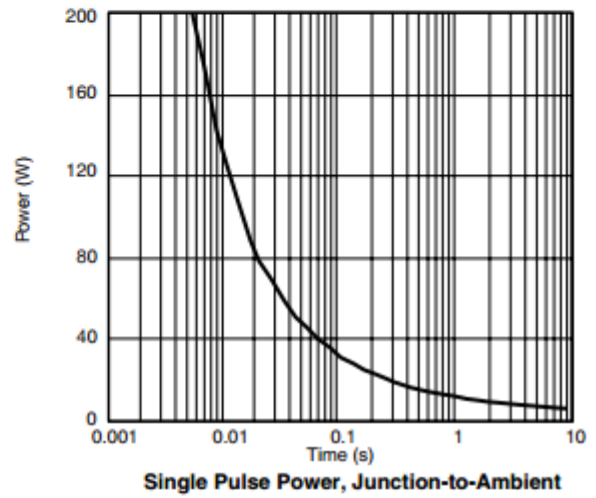
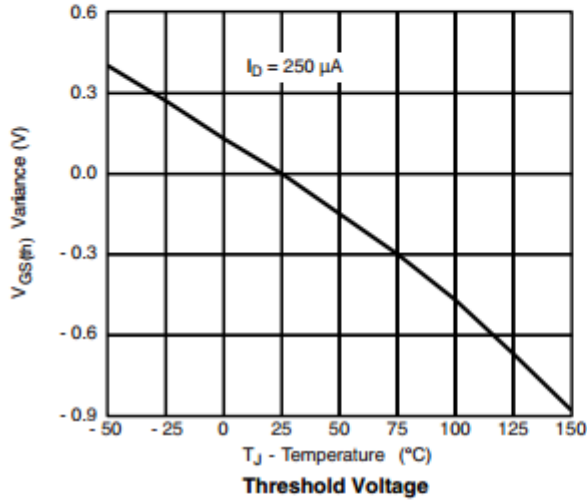


Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71854.